# 2SC4808J

## Silicon NPN epitaxial planar type

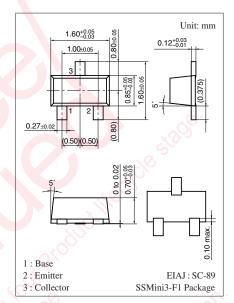
#### For UHF band low-noise amplification

#### ■ Features

- Low noise figure NF
- High forward transfer gain  $|S_{21e}|^2$
- High transition frequency f<sub>T</sub>
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	15	V	
Collector-emitter voltage (Base open)	$V_{CEO}$	10	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	2	V	
Collector current	$I_{C}$	80	mA	
Collector power dissipation	$P_{C}$	125	mW	
Junction temperature	T <sub>j</sub>	125	°C	
Storage temperature	$T_{stg}$	-55 to +125	°C	



Marking Symbol: 3M

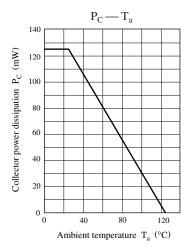
## ■ Electrical Characteristics $T_a = 25$ °C ± 3°C

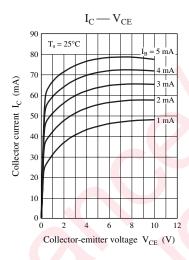
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \mu{\rm A},  I_{\rm E} = 0$	15			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 100 \mu\text{A},  I_B = 0$	10			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 10 \text{ V}, I_E = 0$	1.90		1	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 2 V, I_C = 0$			1	μΑ
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}$	50	150	300	
Transition frequency	$f_T$	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 0.8 \text{ GHz}$	5	6		GHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.7	1.2	pF
Forward transfer gain	S <sub>21e</sub>   2	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 0.8 \text{ GHz}$	11	14		dB
Maximum unilateral power gain	$G_{UM}$	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 0.8 \text{ GHz}$		15		dB
Noise figure	NF <	$V_{CE} = 8 \text{ V}, I_{C} = 7 \text{ mA}, f = 0.8 \text{ GHz}$		1.3	2.0	dB

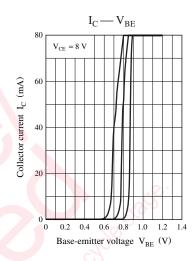
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

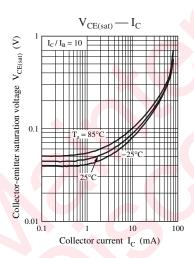
2. \*: Pulse measurement

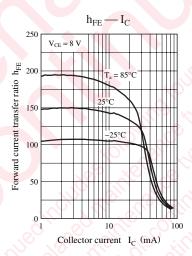
# **Panasonic**

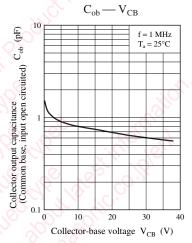












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